

### 5 MHz, 0.5 mA, Zero-Drift Op Amps

#### Features

- High DC Precision:
- V<sub>OS</sub> Drift: ±150 nV/°C
- V<sub>OS</sub>: ±25 μV (maximum)
- A<sub>OL</sub>: 111 dB (minimum, V<sub>DD</sub> = 5.5V)
- PSRR: 110 dB (minimum, V<sub>DD</sub> = 5.5V)
- CMRR: 112 dB (minimum, V<sub>DD</sub> = 5.5V)
- $E_{ni}$ : 0.28  $\mu V_{P-P}$  (typical), f = 0.1 Hz to 10 Hz
- $E_{ni}$ : 0.1  $\mu V_{P-P}$  (typical), f = 0.01 Hz to 1 Hz
- Enhanced EMI Protection:
- Electromagnetic Interference Rejection Ratio (EMIRR) at 1.8 GHz: 101 dB
- · Low Power and Supply Voltages:
  - I<sub>Q</sub>: 0.5 mA/amplifier (typical)
  - Wide supply voltage range: 2.2V to 5.5V
- Small Packages:
  - Singles in SC70, SOT-23
  - Duals in 8-Lead MSOP, 2 x 3 TDFN
  - Quads in 14-Lead TSSOP
- · Easy to Use:
  - Rail-to-rail input/output
  - Gain bandwidth product: 5 MHz (typical)
  - Unity gain stable
- Extended Temperature Range: -40°C to +125°C

#### **Typical Applications**

- Portable Instrumentation
- Sensor Conditioning
- Temperature Measurement
- DC Offset Correction
- Medical Instrumentation

#### **Design Aids**

- · SPICE Macro Models
- FilterLab<sup>®</sup> Software
- Microchip Advanced Part Selector (MAPS)
- Analog Demonstration and Evaluation Boards
- Application Notes

#### **Related Parts**

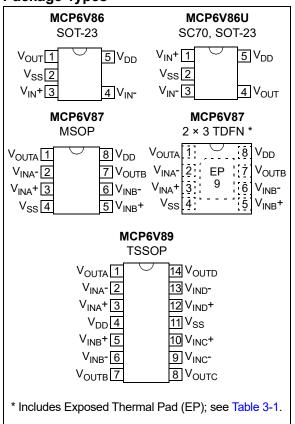
- MCP6V16/6U/7/9: Zero-Drift, Low Power
- MCP6V36/6U/7/9: Zero-Drift, Low Power
- MCP6V66/6U/7/9: Zero-Drift, 1 MHz
- MCP6V76/6U/7/9: Zero-Drift, 2 MHz
- MCP6V91/1U/2/4: Zero-Drift, 10 MHz

#### Description

The Microchip Technology MCP6V86/6U/7/9 family of operational amplifiers provides input offset voltage correction for very low offset and offset drift. These devices have a gain bandwidth product of 5 MHz (typical). They are unity gain stable, have virtually no 1/f noise and have good Power Supply Rejection Ratio (PSRR) and Common-Mode Rejection Ratio (CMRR). These products operate with a single supply voltage, as low as 2.2V, while drawing 500  $\mu$ A/amplifier (typical) of quiescent current.

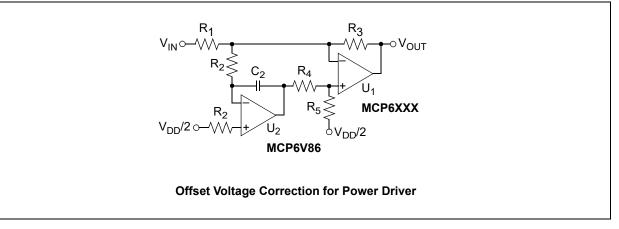
The MCP6V86/6U/7/9 family has enhanced EMI protection to minimize any Electromagnetic Interference from external sources. This feature makes it well-suited for EMI-sensitive applications, such as power lines, radio stations and mobile communications, etc.

The MCP6V86/6U/7/9 op amps are offered in single (MCP6V86 and MCP6V86U), dual (MCP6V87) and quad (MCP6V89) packages. They were designed using an advanced CMOS process.



#### Package Types

#### **Typical Application Circuit**



### 1.0 ELECTRICAL CHARACTERISTICS

#### 1.1 Absolute Maximum Ratings<sup>+</sup>

V <sub>DD</sub> – V <sub>SS</sub>	6.5V
Current at Input Pins	±2 mA
Analog Inputs (V <sub>IN</sub> + and V <sub>IN</sub> -) <sup>(1)</sup>	$V_{SS} - 1.0V$ to $V_{DD} + 1.0V$
All Other Inputs and Outputs	$V_{SS} - 0.3V$ to $V_{DD}$ + 0.3V
Difference Input Voltage	V <sub>DD</sub> – V <sub>SS</sub>
Output Short-Circuit Current	Continuous
Current at Output and Supply Pins	±30 mA
Storage Temperature	65°C to +150°C
Maximum Junction Temperature	+150°C
ESD Protection on All Pins (HBM, CDM, MM)	
MCP6V86/6U	≥ 4 kV, 1.5 kV, 400V
MCP6V87/9	$\ldots \ge 4 \text{ kV}, \ 1.5 \text{ kV}, \ 300 \text{V}$

**†** Notice: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Note 1: See Section 4.2.1 "Rail-to-Rail Inputs".

#### 1.2 Specifications

#### TABLE 1-1: DC ELECTRICAL CHARACTERISTICS

<b>Electrical Characteristics:</b> Unless otherwise indicated, $T_A = +25^{\circ}$ C, $V_{DD} = +2.2$ V to +5.5V, $V_{SS} = $ GND, $V_{CM} = V_{DD}/3$ , $V_{OUT} = V_{DD}/2$ , $V_L = V_{DD}/2$ , $R_L = 10 \text{ k}\Omega$ to $V_L$ and $C_L = 30 \text{ pF}$ (refer to Figures 1-4 and 1-5).								
Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions		
Input Offset								
Input Offset Voltage	V <sub>OS</sub>	-25	_	+25	μV	T <sub>A</sub> = +25°C		
Input Offset Voltage Drift with Temperature (Linear Temperature Coefficient)	TC <sub>1</sub>	-150	_	+150	nV/°C	T <sub>A</sub> = -40 to +125°C, (Note 1)		
Input Offset Voltage Quadratic Temperature Coefficient	TC <sub>2</sub>	—	±30	—	pV/°C <sup>2</sup>	$T_A = -40^{\circ}C \text{ to } +125^{\circ}C$		
Input Offset Voltage Aging	$\Delta V_{OS}$	_	±0.25	_	μV	408 hours Life Test at +150°C, measured at +25°C		
Power Supply Rejection Ratio	PSRR	110	127	—	dB			

Note 1: For design guidance only; not tested.

#### TABLE 1-1: DC ELECTRICAL CHARACTERISTICS (CONTINUED)

$V_{CM} = V_{DD}/3, V_{OUT} = V_{DD}/2, V_{L} = V_{DD}/2, V_{D}/2, V_{D}/2$						
Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions
Input Bias Current and Impedance						-
Input Bias Current	I <sub>B</sub>	-50	±2	+50	pА	
Input Bias Current Across Temperature	Ι <sub>Β</sub>	—	+10	—	pА	T <sub>A</sub> = +85°C
	Ι <sub>Β</sub>	0	+0.24	+1	nA	T <sub>A</sub> = +125°C
Input Offset Current	I <sub>OS</sub>	-400	±100	+400	pА	
Input Offset Current Across Temperature	I <sub>OS</sub>	—	±75	—	pА	T <sub>A</sub> = +85°C
	I <sub>OS</sub>	-500	±100	+500	pА	T <sub>A</sub> = +125°C
Common-Mode Input Impedance	Z <sub>CM</sub>	—	10 <sup>13</sup>   14	—	Ω∥pF	
Differential Input Impedance	Z <sub>DIFF</sub>	—	10 <sup>13</sup>   3	—	Ω∥pF	
Common-Mode						
Common-Mode Input Voltage Range Low	V <sub>CML</sub>	—	—	V <sub>SS</sub> -0.2	V	
Common-Mode Input Voltage Range High	V <sub>CMH</sub>	V <sub>DD</sub> + 0.3	—	_	V	
Common-Mode Rejection Ratio	CMRR	103	128	—	dB	V <sub>DD</sub> = 2.2V, V <sub>CM</sub> = -0.2V to 2.5V
	CMRR	112	136	—	dB	V <sub>DD</sub> = 5.5V, V <sub>CM</sub> = -0.2V to 5.8V
Open-Loop Gain				11		
DC Open-Loop Gain (Large Signal)	A <sub>OL</sub>	97	146	—	dB	V <sub>DD</sub> = 2.2V, V <sub>OUT</sub> = 0.3V to 2.0
	A <sub>OL</sub>	111	151	—	dB	V <sub>DD</sub> = 5.5V, V <sub>OUT</sub> = 0.3V to 5.3
Output				· · ·		
Minimum Output Voltage Swing	V <sub>OL</sub>	V <sub>SS</sub>	V <sub>SS</sub> + 35	V <sub>SS</sub> + 120	mV	$R_L = 1 k\Omega, G = +2,$ 0.5V input overdrive
	V <sub>OL</sub>	—	V <sub>SS</sub> + 5	—	mV	$R_L = 10 k\Omega$ , G = +2 0.5V input overdriv
Maximum Output Voltage Swing	V <sub>OH</sub>	V <sub>DD</sub> – 120	V <sub>DD</sub> – 45	V <sub>DD</sub>	mV	$R_L = 1 k\Omega, G = +2,$ 0.5V input overdriv
	V <sub>OH</sub>	—	V <sub>DD</sub> – 5	-	mV	$R_L = 10 k\Omega$ , G = +2 0.5V input overdriv
Output Short-Circuit Current	I <sub>SC</sub>		±15		mA	V <sub>DD</sub> = 2.2V
	I <sub>SC</sub>		±40		mA	V <sub>DD</sub> = 5.5V
Power Supply						
Supply Voltage	V <sub>DD</sub>	2.2	_	5.5	V	
Quiescent Current per Amplifier	I <sub>Q</sub>	250	500	770	μA	I <sub>O</sub> = 0
Power-on Reset (POR) Trip Voltage	V <sub>POR</sub>	1.2	1.6	1.9	V	

Note 1: For design guidance only; not tested.

<b>Electrical Characteristics:</b> Unless otherwise indicated, $T_A = +25^{\circ}C$ , $V_{DD} = +2.2V$ to +5.5V, $V_{SS} = GND$ , $V_{CM} = V_{DD}/3$ , $V_{OUT} = V_{DD}/2$ , $V_L = V_{DD}/2$ , $R_L = 10 \text{ k}\Omega$ to $V_L$ and $C_L = 30 \text{ pF}$ (refer to Figures 1-4 and 1-5).								
Parameters	Sym.	Min.	Тур.		Units	Conditions		
Amplifier AC Response								
Gain Bandwidth Product	GBWP	_	5		MHz			
Slew Rate	SR	_	4		V/µs			
Phase Margin	PM		60		°C	G = +1		
Amplifier Noise Response			•					
Input Noise Voltage	E <sub>ni</sub>	_	0.1	_	μV <sub>P-P</sub>	f = 0.01 Hz to 1 Hz		
	E <sub>ni</sub>		0.28	—	μV <sub>P-P</sub>	f = 0.1 Hz to 10 Hz		
Input Noise Voltage Density	e <sub>ni</sub>		13	_	nV/√Hz	f < 2 kHz		
Input Noise Current Density	i <sub>ni</sub>	_	6	_	fA/√Hz			
Amplifier Distortion <sup>(1)</sup>			•					
Intermodulation Distortion (AC)	IMD	—	100	—	μV <sub>PK</sub>	V <sub>CM</sub> tone = 100 mV <sub>PK</sub> at 1 kHz, G <sub>N</sub> = 11, RTI		
Amplifier Step Response								
Start-up Time	t <sub>STR</sub>	_	100		μs	G = +1, 0.1% V <sub>OUT</sub> settling (Note 2)		
Offset Correction Settling Time	t <sub>STL</sub>	_	30	_	μs	G = +1, V <sub>IN</sub> step of 2V, V <sub>OS</sub> within 100 μV of its final value		
Output Overdrive Recovery Time	t <sub>ODR</sub>		60	—	μs	G = -10, $\pm 0.5$ V input overdrive to V <sub>DD</sub> /2, V <sub>IN</sub> 50% point to V <sub>OUT</sub> 90% point (Note 3)		
EMI Protection			•					
EMI Rejection Ratio	EMIRR		90		dB	V <sub>IN</sub> = 0.1 V <sub>PK</sub> , f = 400 MHz		
		_	100	—		V <sub>IN</sub> = 0.1 V <sub>PK</sub> , f = 900 MHz		
			101	—		V <sub>IN</sub> = 0.1 V <sub>PK</sub> , f = 1800 MHz		
		_	105	—		V <sub>IN</sub> = 0.1 V <sub>PK</sub> , f = 2400 MHz		

#### TABLE 1-2: AC ELECTRICAL CHARACTERISTICS

Note 1: These parameters were characterized using the circuit in Figure 1-6. In Figures 2-36 and 2-37, there is an IMD tone at DC, a residual tone at 1 kHz, and other IMD tones and clock tones. IMD is Referred to Input (RTI).

2: High gains behave differently; see Section 4.3.2 "Offset at Power-up".

3: t<sub>STL</sub> and t<sub>ODR</sub> include some uncertainty due to clock edge timing.

#### TABLE 1-3: TEMPERATURE SPECIFICATIONS

<b>Electrical Characteristics:</b> Unless otherwise indicated, all limits are specified for: $V_{DD}$ = +2.2V to +5.5V, $V_{SS}$ = GND.									
Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions			
Temperature Ranges									
Specified Temperature Range	T <sub>A</sub>	-40	—	+125	°C				
Operating Temperature Range	T <sub>A</sub>	-40	—	+125	°C	Note 1			
Storage Temperature Range	T <sub>A</sub>	-65	—	+150	°C				
Thermal Package Resistances									
Thermal Resistance, 5-Lead SC70	$\theta_{JA}$	—	209	—	°C/W				
Thermal Resistance, 5-Lead SOT-23	$\theta_{JA}$	—	201	—	°C/W				
Thermal Resistance, 8-Lead 2x3 TDFN	$\theta_{JA}$	_	53		°C/W				
Thermal Resistance, 8-Lead MSOP	$\theta_{JA}$	_	211	_	°C/W				
Thermal Resistance, 14-Lead TSSOP	$\theta_{JA}$	—	100	—	°C/W				

**Note 1:** Operation must not cause  $T_J$  to exceed Maximum Junction Temperature specification (+150°C).

#### 1.3 Timing Diagrams

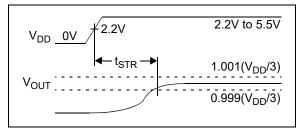


FIGURE 1-1: Amplifier Start-up.

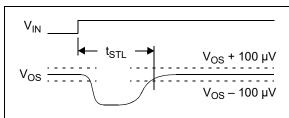
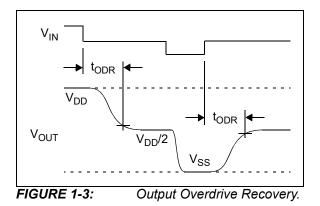
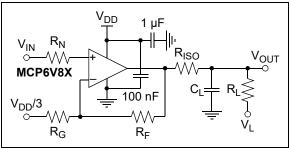


FIGURE 1-2: Offset Correction Settling Time.

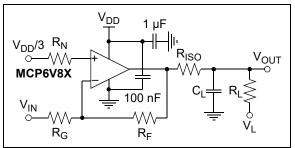


#### 1.4 Test Circuits

The circuits used for most DC and AC tests are shown in Figures 1-4 and 1-5. Lay the bypass capacitors out as discussed in **Section 4.3.9** "Supply Bypassing and Filtering".  $R_N$  is equal to the parallel combination of  $R_F$  and  $R_G$  to minimize bias current effects.

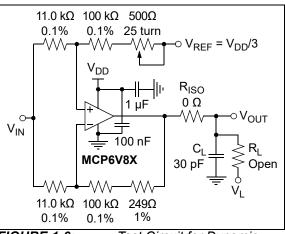


**FIGURE 1-4:** AC and DC Test Circuit for Most Noninverting Gain Conditions.



**FIGURE 1-5:** AC and DC Test Circuit for Most Inverting Gain Conditions.

The circuit in Figure 1-6 tests the input's dynamic behavior (i.e., IMD,  $t_{STR}$ ,  $t_{STL}$  and  $t_{ODR}$ ). The potentiometer balances the resistor network ( $V_{OUT}$  should equal  $V_{REF}$  at DC). The op amp's Common-mode input voltage is  $V_{CM} = V_{IN}/2$ . The error at the input ( $V_{ERR}$ ) appears at  $V_{OUT}$  with a noise gain of 10 V/V.



**FIGURE 1-6:** Test Circuit for Dynamic Input Behavior.

#### 2.0 TYPICAL PERFORMANCE CURVES

**Note:** The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

**Note:** Unless otherwise indicated,  $T_A = +25^{\circ}$ C,  $V_{DD} = +2.2$ V to 5.5V,  $V_{SS} = GND$ ,  $V_{CM} = V_{DD}/3$ ,  $V_{OUT} = V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10 \text{ k}\Omega$  to  $V_L$  and  $C_L = 30 \text{ pF}$ .

#### 2.1 DC Input Precision

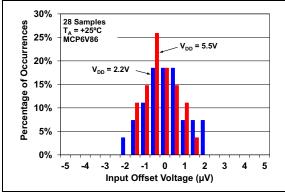
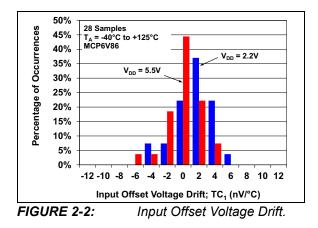


FIGURE 2-1:

Input Offset Voltage.



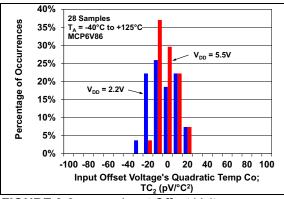
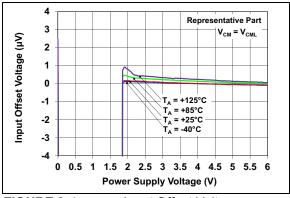
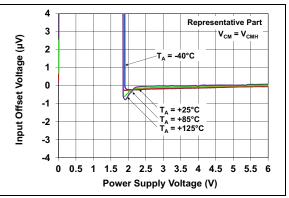


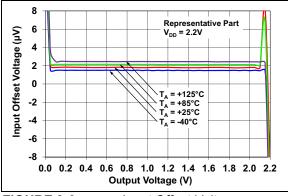
FIGURE 2-3: Input Offset Voltage Quadratic Temperature Coefficient.

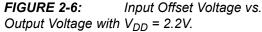


**FIGURE 2-4:** Input Offset Voltage vs. Power Supply Voltage with  $V_{CM} = V_{CML}$ .

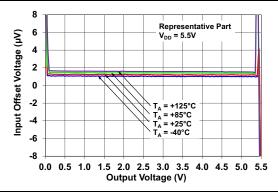


**FIGURE 2-5:** Input Offset Voltage vs. Power Supply Voltage with  $V_{CM} = V_{CMH}$ .





**Note:** Unless otherwise indicated,  $T_A = +25$ °C,  $V_{DD} = +2.2V$  to 5.5V,  $V_{SS} = GND$ ,  $V_{CM} = V_{DD}/3$ ,  $V_{OUT} = V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10 \text{ k}\Omega$  to  $V_L$  and  $C_L = 30 \text{ pF}$ .



**FIGURE 2-7:** Input Offset Voltage vs. Output Voltage with  $V_{DD} = 5.5V$ .

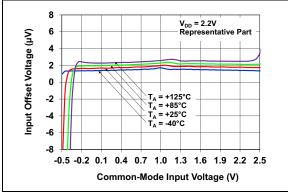
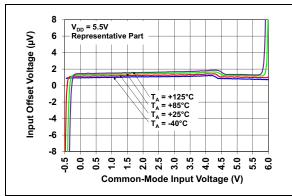
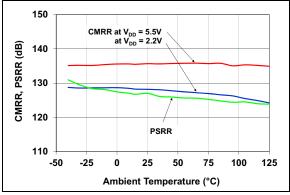


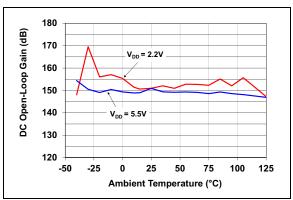
FIGURE 2-8:Input Offset Voltage vs.Common-Mode Voltage with  $V_{DD} = 2.2V.$ 



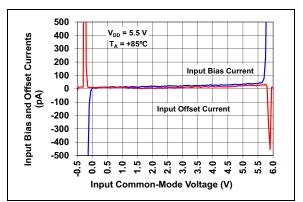
**FIGURE 2-9:** Input Offset Voltage vs. Common-Mode Voltage with  $V_{DD} = 5.5V$ .



**FIGURE 2-10:** CMRR and PSRR vs. Ambient Temperature.

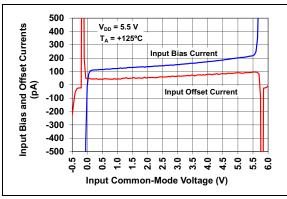


*FIGURE 2-11:* DC Open-Loop Gain vs. Ambient Temperature.

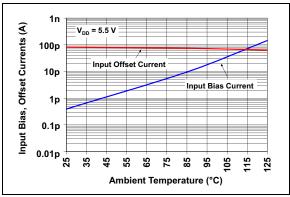


**FIGURE 2-12:** Input Bias and Offset Currents vs. Common-Mode Input Voltage with  $T_A = +85^{\circ}C$ .

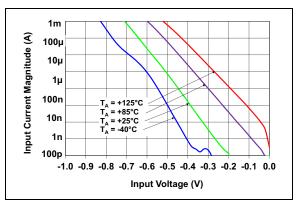
**Note:** Unless otherwise indicated,  $T_A = +25^{\circ}C$ ,  $V_{DD} = +2.2V$  to 5.5V,  $V_{SS} = GND$ ,  $V_{CM} = V_{DD}/3$ ,  $V_{OUT} = V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10 \text{ k}\Omega$  to  $V_L$  and  $C_L = 30 \text{ pF}$ .



**FIGURE 2-13:** Input Bias and Offset Currents vs. Common-Mode Input Voltage with  $T_A = +125$ °C.



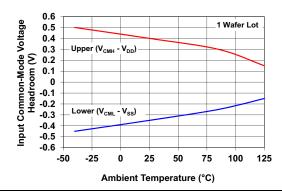
**FIGURE 2-14:** Input Bias and Offset Currents vs. Ambient Temperature with  $V_{DD} = 5.5V$ .



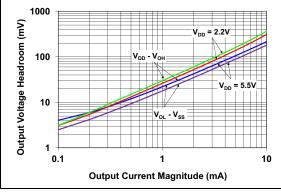
**FIGURE 2-15:** Input Bias Current vs. Input Voltage (Below  $V_{SS}$ ).

**Note:** Unless otherwise indicated,  $T_A = +25^{\circ}C$ ,  $V_{DD} = +2.2V$  to 5.5V,  $V_{SS} = GND$ ,  $V_{CM} = V_{DD}/3$ ,  $V_{OUT} = V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10 \text{ k}\Omega$  to  $V_L$  and  $C_L = 30 \text{ pF}$ .

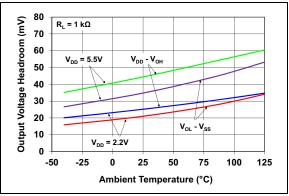
#### 2.2 Other DC Voltages and Currents



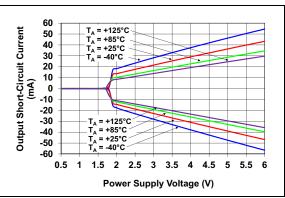
**FIGURE 2-16:** Input Common-Mode Voltage Headroom (Range) vs. Ambient Temperature.



**FIGURE 2-17:** Output Voltage Headroom vs. Output Current.



*FIGURE 2-18:* Output Voltage Headroom vs. Ambient Temperature.



**FIGURE 2-19:** Output Short-Circuit Current vs. Power Supply Voltage.

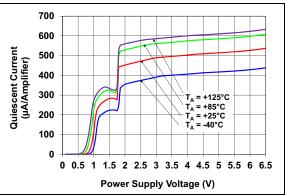
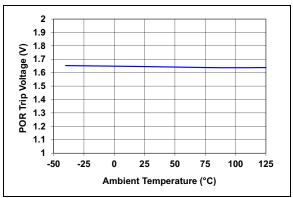


FIGURE 2-20: Supply Current vs. Power Supply Voltage.



**FIGURE 2-21:** Power-on Reset Voltage vs. Ambient Temperature.

**Note:** Unless otherwise indicated,  $T_A = +25^{\circ}$ C,  $V_{DD} = +2.2$ V to 5.5V,  $V_{SS} = GND$ ,  $V_{CM} = V_{DD}/3$ ,  $V_{OUT} = V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10 \text{ k}\Omega$  to  $V_L$  and  $C_L = 30 \text{ pF}$ .

#### 2.3 Frequency Response

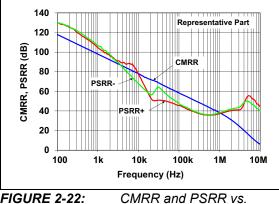
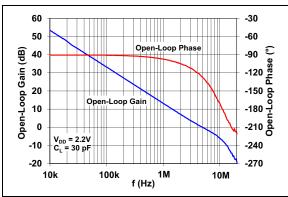
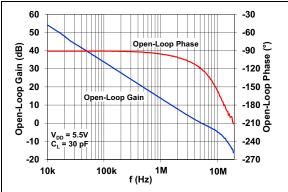


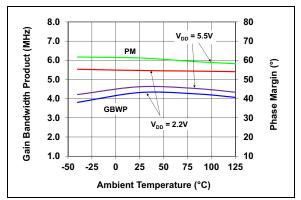
FIGURE 2-22: Frequency.



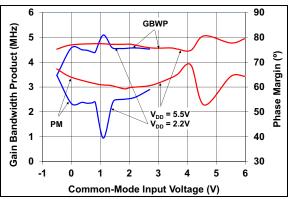
**FIGURE 2-23:** Open-Loop Gain vs. Frequency with  $V_{DD}$  = 2.2V.



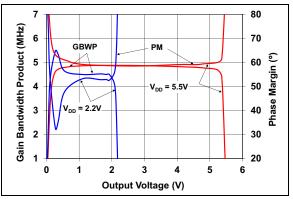
**FIGURE 2-24:** Open-Loop Gain vs. Frequency with  $V_{DD} = 5.5V$ .



**FIGURE 2-25:** Gain Bandwidth Product and Phase Margin vs. Ambient Temperature.

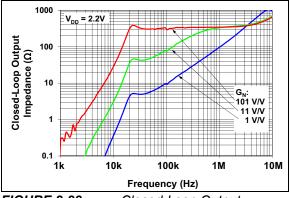


**FIGURE 2-26:** Gain Bandwidth Product and Phase Margin vs. Common-Mode Input Voltage.

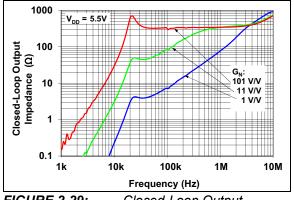


**FIGURE 2-27:** Gain Bandwidth Product and Phase Margin vs. Output Voltage.

**Note:** Unless otherwise indicated,  $T_A = +25$ °C,  $V_{DD} = +2.2V$  to 5.5V,  $V_{SS} = GND$ ,  $V_{CM} = V_{DD}/3$ ,  $V_{OUT} = V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10 \text{ k}\Omega$  to  $V_L$  and  $C_L = 30 \text{ pF}$ .



**FIGURE 2-28:** Closed-Loop Output Impedance vs. Frequency with  $V_{DD} = 2.2V$ .



**FIGURE 2-29:** Closed-Loop Output Impedance vs. Frequency with  $V_{DD} = 5.5V$ .

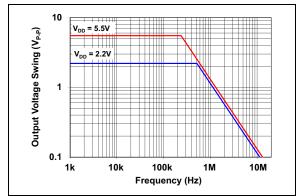
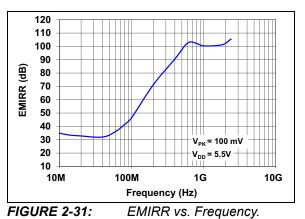


FIGURE 2-30: Maximum Output Voltage Swing vs. Frequency.



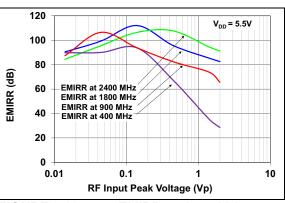


FIGURE 2-32: EMIRR vs. Input Voltage.

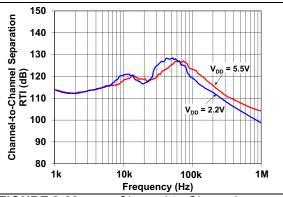


FIGURE 2-33: Channel-to-Channel Separation vs. Frequency.

**Note:** Unless otherwise indicated,  $T_A = +25^{\circ}C$ ,  $V_{DD} = +2.2V$  to 5.5V,  $V_{SS} = GND$ ,  $V_{CM} = V_{DD}/3$ ,  $V_{OUT} = V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10 \text{ k}\Omega$  to  $V_L$  and  $C_L = 30 \text{ pF}$ .

#### 2.4 Input Noise and Distortion

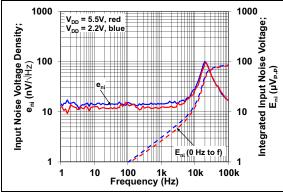


FIGURE 2-34: Input Noise Voltage Density and Integrated Input Noise Voltage vs. Frequency.

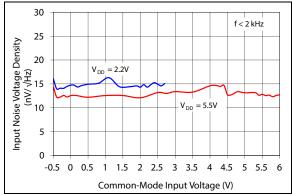
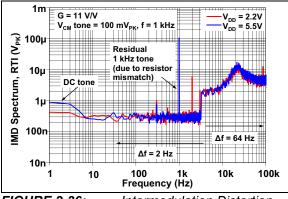
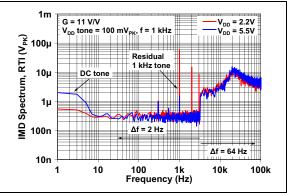


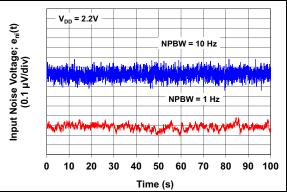
FIGURE 2-35: Input Noise Voltage Density vs. Input Common-Mode Voltage.



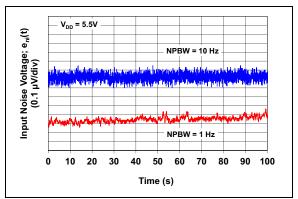
**FIGURE 2-36:** Intermodulation Distortion vs. Frequency with  $V_{CM}$  Disturbance (see Figure 1-6).



**FIGURE 2-37:** Intermodulation Distortion vs. Frequency with  $V_{DD}$  Disturbance (see Figure 1-6).



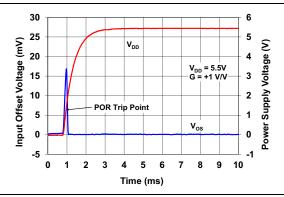
**FIGURE 2-38:** Input Noise vs. Time with 1 Hz and 10 Hz Filters and  $V_{DD} = 2.2V$ .



**FIGURE 2-39:** Input Noise vs. Time with 1 Hz and 10 Hz Filters and  $V_{DD}$  = 5.5V.

**Note:** Unless otherwise indicated,  $T_A = +25^{\circ}C$ ,  $V_{DD} = +2.2V$  to 5.5V,  $V_{SS} = GND$ ,  $V_{CM} = V_{DD}/3$ ,  $V_{OUT} = V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10 \text{ k}\Omega$  to  $V_L$  and  $C_L = 30 \text{ pF}$ .

#### 2.5 Time Response



**FIGURE 2-40:** Input Offset Voltage vs. Time at Power-up.

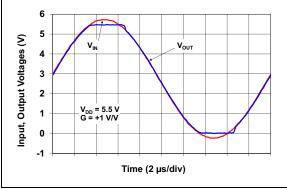


FIGURE 2-41: The MCP6V86/6U/7/9 Family Shows No Input Phase Reversal with Overdrive.

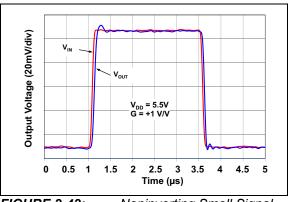


FIGURE 2-42: Step Response.

Noninverting Small Signal

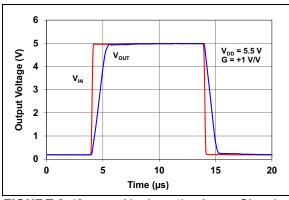


FIGURE 2-43: Noninverting Large Signal Step Response.

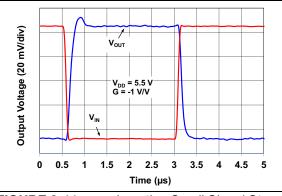
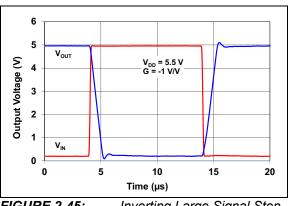
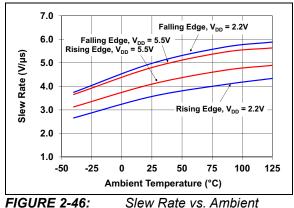


FIGURE 2-44: Inverting Small Signal Step Response.

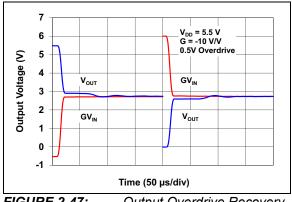


**FIGURE 2-45:** Inverting Large Signal Step Response.

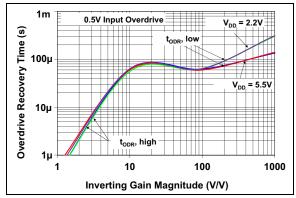
**Note:** Unless otherwise indicated,  $T_A = +25^{\circ}C$ ,  $V_{DD} = +2.2V$  to 5.5V,  $V_{SS} = GND$ ,  $V_{CM} = V_{DD}/3$ ,  $V_{OUT} = V_{DD}/2$ ,  $V_L = V_{DD}/2$ ,  $R_L = 10 \text{ k}\Omega$  to  $V_L$  and  $C_L = 30 \text{ pF}$ .



Temperature.



**FIGURE 2-47:** Output Overdrive Recovery vs. Time with G = -10 V/V.



**FIGURE 2-48:** Output Overdrive Recovery Time vs. Inverting Gain.

NOTES:

#### 3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 3-1.

MCP6V86	MCP6V86U	MCP	6V87	MCP6V89		
SOT-23	SOT-23, SC70	2x3 TDFN	MSOP	TSSOP	Symbol	Description
1	4	1	1	1	V <sub>OUT</sub>	Output
4	3	2	2	2	V <sub>IN</sub> -	Inverting Input
3	1	3	3	3	V <sub>IN</sub> +	Noninverting Input
5	5	8	8	4	V <sub>DD</sub>	Positive Power Supply
_	_	5	5	5	V <sub>INB</sub> +	Noninverting Input (Op Amp B)
_	_	6	6	6	V <sub>INB</sub> -	Inverting Input (Op Amp B)
_	_	7	7	7	V <sub>OUTB</sub>	Output (Op Amp B)
_	_	—	_	8	V <sub>OUTC</sub>	Output (Op Amp C)
_	_	_		9	V <sub>INC</sub> -	Inverting Input (Op Amp C)
_	_	—		10	V <sub>INC</sub> +	Noninverting Input (Op Amp C)
2	2	4	4	11	V <sub>SS</sub>	Negative Power Supply
_	_	—	—	12	V <sub>IND</sub> +	Noninverting Input (Op Amp D)
_		—		13	V <sub>IND</sub> -	Inverting Input (Op Amp D)
_	_	_		14	V <sub>OUTD</sub>	Output (Op Amp D)
	—	9		—	EP	Exposed Thermal Pad (EP); must be connected to V <sub>SS</sub>

#### TABLE 3-1: PIN FUNCTION TABLE

## 3.1 Analog Outputs (V<sub>OUT</sub>, V<sub>OUTA</sub>, V<sub>OUTB</sub>, V<sub>OUTC</sub>, V<sub>OUTD</sub>)

The analog output pins are low-impedance voltage sources.

## 3.2 Analog Inputs ( $V_{IN}$ -, $V_{IN}$ +, $V_{INB}$ +, $V_{INB}$ -, $V_{INC}$ -, $V_{INC}$ +, $V_{IND}$ +, $V_{IND}$ -)

The noninverting and inverting inputs are high-impedance CMOS inputs with low bias currents.

#### 3.3 Power Supply Pins (V<sub>DD</sub>, V<sub>SS</sub>)

The positive power supply ( $V_{DD}$ ) is 2.2V to 5.5V higher than the negative power supply ( $V_{SS}$ ). For normal operation, the other pins are between  $V_{SS}$  and  $V_{DD}$ .

Typically, these parts are used in a single (positive) supply configuration. In this case,  $V_{SS}$  is connected to ground and  $V_{DD}$  is connected to the supply.  $V_{DD}$  will need bypass capacitors.

#### 3.4 Exposed Thermal Pad (EP)

There is an internal connection between the exposed thermal pad (EP) and the  $V_{SS}$  pin; it must be connected to the same potential on the Printed Circuit Board (PCB).

This pad can be connected to a PCB ground plane to provide a larger heat sink. This improves the package thermal resistance ( $\theta_{JA}$ ).

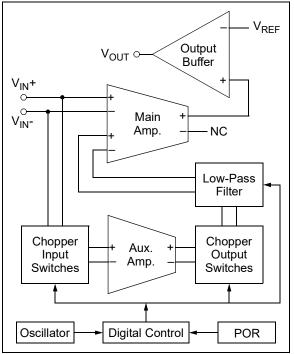
NOTES:

#### 4.0 APPLICATIONS

The MCP6V86/6U/7/9 family of zero-drift op amps is manufactured using Microchip's state-of-the-art CMOS process. It is designed for precision applications with requirements for small packages and low power. The low supply voltage and low quiescent current make the MCP6V86/6U/7/9 devices ideal for battery-powered applications.

#### 4.1 Overview of Zero-Drift Operation

Figure 4-1 shows a simplified diagram of the MCP6V86/6U/7/9 zero-drift op amp. This diagram will be used to explain how slow voltage errors are reduced in this architecture (much better  $V_{OS}$ ,  $\Delta V_{OS}/\Delta T_A$  (TC<sub>1</sub>), CMRR, PSRR, A<sub>OL</sub> and 1/f noise).



**FIGURE 4-1:** Simplified Zero-Drift Op Amp Functional Diagram.

#### 4.1.1 BUILDING BLOCKS

The main amplifier is designed for high gain and bandwidth, with a differential topology. Its main input pair (+ and – pins at the top left) is used for the higher frequency portion of the input signal. Its auxiliary input pair (+ and – pins at the bottom left) is used for the low-frequency portion of the input signal and corrects the op amp's input offset voltage. Both inputs are added together internally.

The auxiliary amplifier, chopper input switches and chopper output switches provide a high DC gain to the input signal. DC errors are modulated to higher frequencies, while white noise is modulated to a low frequency. The low-pass filter reduces high-frequency content, including harmonics of the chopping clock.

The output buffer drives external loads at the  $V_{\text{OUT}}$  pin (V\_{\text{REF}} is an internal reference voltage).

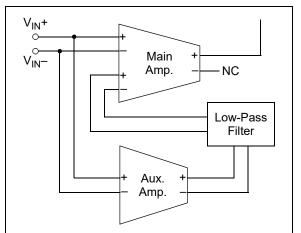
The oscillator runs at  $f_{OSC1}$  = 200 kHz. Its output is divided by two, to produce the chopping clock rate of  $f_{CHOP}$  = 100 kHz.

The internal Power-on Reset (POR) starts the part in a known good state, protecting against power supply brown-outs.

The digital control block controls switching and POR events.

#### 4.1.2 CHOPPING ACTION

Figure 4-2 shows the amplifier connections for the first phase of the chopping clock and Figure 4-3 shows the connections for the second phase. Its slow voltage errors alternate in polarity, making the average error small.



**FIGURE 4-2:** First Chopping Clock Phase; Equivalent Amplifier Diagram.

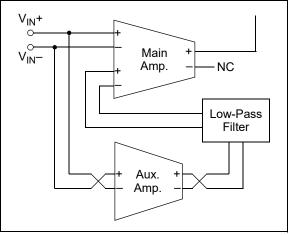


FIGURE 4-3: Second Chopping Clock Phase; Equivalent Amplifier Diagram.

### 4.1.3 INTERMODULATION DISTORTION (IMD)

These op amps will show IMD products when an AC signal is present.

The signal and clock can be decomposed into sine wave tones (Fourier series components). These tones interact with the zero-drift circuitry's nonlinear response to produce IMD tones at sum and difference frequencies. Each of the square wave clock's harmonics has a series of IMD tones centered on it (see Figures 2-36 and 2-37).

#### 4.2 Other Functional Blocks

#### 4.2.1 RAIL-TO-RAIL INPUTS

The input stage of the MCP6V86/6U/7/9 op amps uses two differential CMOS input stages in parallel. One operates at low Common-mode Input Voltage (V<sub>CM</sub>, which is approximately equal to V<sub>IN</sub>+ and V<sub>IN</sub>- in normal operation) and the other operates at high V<sub>CM</sub>. With this topology, the input operates with V<sub>CM</sub> up to V<sub>DD</sub> + 0.3V and down to V<sub>SS</sub> - 0.2V, at +25°C (see Figure 2-16). The input Offset Voltage (V<sub>OS</sub>) is measured at V<sub>CM</sub> = V<sub>SS</sub> - 0.2V and V<sub>DD</sub> + 0.3V to ensure proper operation.

#### 4.2.1.1 Phase Reversal

The input devices are designed to not exhibit phase inversion when the input pins exceed the supply voltages. Figure 2-41 shows an input voltage exceeding both supplies with no phase inversion.

#### 4.2.1.2 Input Voltage Limits

In order to prevent damage and/or improper operation of these amplifiers, the circuit must limit the voltages at the input pins (see Section 1.1 "Absolute Maximum Ratings†"). This requirement is independent of the input current limits discussed later on.

The ESD protection on the inputs can be depicted as shown in Figure 4-4. This structure was chosen to protect the input transistors against many (but not all) overvoltage conditions and to minimize Input Bias ( $I_B$ ) current.

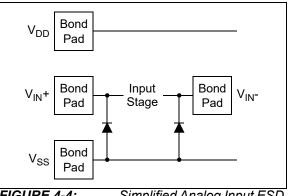
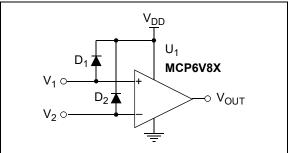


FIGURE 4-4: Simplified Analog Input ESD Structures.

The input ESD diodes clamp the inputs when they try to go more than one diode drop below  $V_{SS}$ . They also clamp any voltages well above  $V_{DD}$ ; their breakdown voltage is high enough to allow normal operation, but not low enough to protect against slow overvoltage (beyond  $V_{DD}$ ) events. Very fast ESD events (that meet the specification) are limited so that damage does not occur.

In some applications, it may be necessary to prevent excessive voltages from reaching the op amp inputs; Figure 4-5 shows one approach to protecting these inputs.  $D_1$  and  $D_2$  may be small signal silicon diodes, Schottky diodes for lower clamping voltages or diode-connected FETs for low leakage.

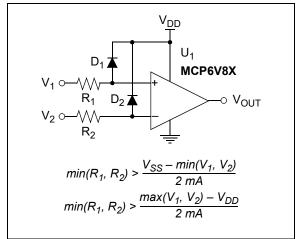


**FIGURE 4-5:** Protecting the Analog Inputs Against High Voltages.

#### 4.2.1.3 Input Current Limits

In order to prevent damage and/or improper operation of these amplifiers, the circuit must limit the currents into the input pins (see Section 1.1 "Absolute Maximum Ratings†"). This requirement is independent of the voltage limits discussed previously.

Figure 4-6 shows one approach to protecting these inputs. The  $R_1$  and  $R_2$  resistors limit the possible current in or out of the input pins (and into  $D_1$  and  $D_2$ ). The diode currents will dump onto  $V_{DD}$ .



**FIGURE 4-6:** Protecting the Analog Inputs Against High Currents.

It is also possible to connect the diodes to the left of the  $R_1$  and  $R_2$  resistors. In this case, the currents through the  $D_1$  and  $D_2$  diodes need to be limited by some other mechanism. The resistors then serve as inrush current limiters; the DC current into the input pins ( $V_{IN}\text{+}$  and  $V_{IN}\text{-}$ ) should be very small.

A significant amount of current can flow out of the inputs (through the ESD diodes) when the Common-mode Input Voltage (V<sub>CM</sub>) is below ground (V<sub>SS</sub>); see Figure 2-15.

#### 4.2.2 RAIL-TO-RAIL OUTPUT

The output voltage range of the MCP6V86/6U/7/9 devices' zero-drift op amps is V<sub>DD</sub> – 5 mV (typical), and V<sub>SS</sub> + 5 mV (typical) when R<sub>L</sub> = 10 k $\Omega$  is connected to V<sub>DD</sub>/2 and V<sub>DD</sub> = 5.5V. Refer to Figures 2-17 and 2-18 for more information.

This op amp is designed to drive light loads; use another amplifier to buffer the output from heavy loads.

#### 4.3 Application Tips

#### 4.3.1 INPUT OFFSET VOLTAGE OVER TEMPERATURE

Table 1-1 gives both the linear and quadratic Temperature Coefficients ( $TC_1$  and  $TC_2$ ) of the input offset voltage. The input offset voltage, at any temperature in the specified range, can be calculated as follows:

**EQUATION 4-1:** 

V <sub>O</sub>	$S(T_{A})$	$A_{1} = V_{OS} + TC_{I}\Delta T + TC_{2}\Delta T^{2}$
Where:		
$\Delta T$	=	T <sub>A</sub> – +25°C
$V_{OS}(T_A)$	=	Input offset voltage at T <sub>A</sub>
$V_{OS}$	=	Input offset voltage at +25°C
$TC_{I}$	=	Linear temperature coefficient
$TC_2$	=	Quadratic temperature coefficient

#### 4.3.2 OFFSET AT POWER-UP

When these parts power up, the Input Offset ( $V_{OS}$ ) starts at its uncorrected value. Circuits with high DC gain can cause the output to reach one of the two rails. In this case, the time to a valid output is delayed by an Output Overdrive Time (like  $t_{ODR}$ ) in addition to the Start-up Time (like  $t_{STR}$ ).

It can be simple to avoid this extra start-up time. Reducing the gain is one method; adding a capacitor across the Feedback Resistor ( $R_F$ ) is another method.

#### 4.3.3 SOURCE RESISTANCES

The input bias currents have two significant components: switching glitches that dominate at room temperature and below, and input ESD diode leakage currents that dominate at +85°C and above.

Make the resistances seen by the inputs small and equal. This minimizes the output offset caused by the input bias currents.

The inputs should see a resistance on the order of  $10\Omega$  to 1 k $\Omega$  at high frequencies (i.e., above 1 MHz). This helps minimize the impact of switching glitches, which are very fast, on overall performance. In some cases, it may be necessary to add resistors in series with the inputs to achieve this improvement in performance.

Small input resistances may be needed for high gains. Without them, parasitic capacitances might cause positive feedback and instability.

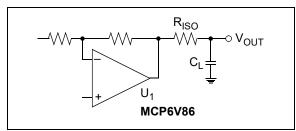
#### 4.3.4 SOURCE CAPACITANCE

The capacitances seen by the two inputs should be small. Large input capacitances and source resistances, together with high gain, can lead to positive feedback and instability.

#### 4.3.5 CAPACITIVE LOADS

Driving large capacitive loads can cause stability problems for voltage feedback op amps. As the load capacitance increases, the feedback loop's phase margin decreases and the closed-loop bandwidth is reduced. This produces gain peaking in the frequency response, with overshoot and ringing in the step response. These zero-drift op amps have a different output impedance than most op amps due to their unique topology.

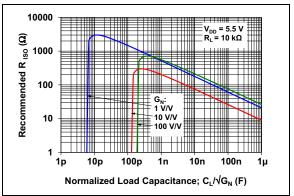
When driving a capacitive load with these op amps, a series resistor at the output ( $R_{ISO}$  in Figure 4-7) improves the feedback loop's phase margin (stability) by making the output load resistive at higher frequencies. The bandwidth will be generally lower than the bandwidth with no capacitive load.



**FIGURE 4-7:** Output Resistor, R<sub>ISO</sub>, Stabilizes Capacitive Loads.

Figure 4-8 gives recommended  $R_{ISO}$  values for different capacitive loads and gains. The x-axis is the Load Capacitance ( $C_L$ ). The y-axis is the resistance ( $R_{ISO}$ ).

 $G_N$  is the circuit's Noise Gain. For noninverting gains,  $G_N$  and the Signal Gain are equal. For inverting gains,  $G_N$  is 1+|Signal Gain| (e.g., -1 V/V gives  $G_N$  = +2V/V).



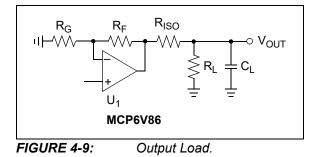
**FIGURE 4-8:** Recommended R<sub>ISO</sub> Values for Capacitive Loads.

After selecting  $R_{ISO}$  for your circuit, double check the resulting frequency response peaking and step response overshoot. Modify the  $R_{ISO}$  value until the response is reasonable. Bench evaluation is helpful.

#### 4.3.6 STABILIZING OUTPUT LOADS

This family of zero-drift op amps has an output impedance that has a double zero when the gain is low (see Figures 2-28 and 2-29). This can cause a large phase shift in feedback networks that have low-impedance near the part's bandwidth. This large phase shift can cause stability problems.

Figure 4-9 shows that the load on the output is:  $(R_L + R_{ISO})||(R_F + R_G)$ , where  $R_{ISO}$  is before the load (like Figure 4-7). This load needs to be large enough to maintain stability; it should be at least 10 k $\Omega$ .



#### 4.3.7 GAIN PEAKING

Figure 4-10 shows an op amp circuit that represents noninverting amplifiers ( $V_M$  is a DC voltage and  $V_P$  is the input) or inverting amplifiers ( $V_P$  is a DC voltage and  $V_M$  is the input). The  $C_N$  and  $C_G$  capacitances represent the total capacitance at the input pins; they include the op amp's Common-mode input capacitance ( $C_{CM}$ ), board parasitic capacitance and any capacitor placed in parallel. The  $C_{FP}$  capacitance represents the parasitic capacitance coupling the output and noninverting input pins.

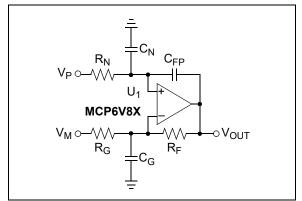


FIGURE 4-10: Amplifier with Parasitic Capacitance.

 $C_G$  acts in parallel with  $R_G$  (except for a gain of +1 V/V), which causes an increase in gain at high frequencies.  $C_G$  also reduces the phase margin of the feedback loop, which becomes less stable. This effect can be reduced by reducing either  $C_G$  or  $R_F || R_G$ .

 $C_N$  and  $R_N$  form a low-pass filter that affects the signal at  $V_P$ . This filter has a single real pole at  $1/(2\pi R_N C_N)$ .

The largest value of R<sub>F</sub> that should be used depends on noise gain (see G<sub>N</sub> in **Section 4.3.5 "Capacitive Loads**"), C<sub>G</sub> and the open-loop gain's phase shift. An approximate limit for R<sub>F</sub> is:

#### **EQUATION 4-2:**

$$R_F \le 10 \, k \, \Omega \times \frac{3.5 \, pF}{C_G} \times G_N^2$$

Some applications may modify these values to reduce either output loading or gain peaking (step response overshoot).

At high gains,  $R_{\rm N}$  needs to be small in order to prevent positive feedback and oscillations. Large  $C_{\rm N}$  values can also help.

#### 4.3.8 REDUCING UNDESIRED NOISE AND SIGNALS

Reduce undesired noise and signals with:

- · Low Bandwidth Signal Filters:
  - Minimize random analog noise
  - Reduce interfering signals
- · Good PCB Layout Techniques:
  - Minimize crosstalk
  - Minimize parasitic capacitances and inductances that interact with fast switching edges
- Good Power Supply Design:
  - Isolation from other parts
  - Filtering of interference on supply line(s)

#### 4.3.9 SUPPLY BYPASSING AND FILTERING

With this family of operational amplifiers, the power supply pin ( $V_{DD}$  for single supply) should have a local bypass capacitor (i.e., 0.01 µF to 0.1 µF) within 2 mm of the pin for good high-frequency performance.

These parts also need a bulk capacitor (i.e., 1  $\mu$ F or larger) within 100 mm to provide large, slow currents. This bulk capacitor can be shared with other low noise analog parts.

In some cases, high-frequency power supply noise (e.g., Switched Mode Power Supplies) may cause undue intermodulation distortion with a DC offset shift; this noise needs to be filtered. Adding a small resistor into the supply connection can be helpful.

#### 4.3.10 PCB DESIGN FOR DC PRECISION

In order to achieve DC precision on the order of  $\pm 1 \mu$ V, many physical errors need to be minimized. The design of the PCB, the wiring and the thermal environment have a strong impact on the precision achieved. A poor PCB design can easily be more than 100 times worse than the MCP6V86/6U/7/9 op amps' minimum and maximum specifications.

#### 4.3.10.1 PCB Layout

Any time two dissimilar metals are joined together, a temperature-dependent voltage appears across the junction (the Seebeck or thermojunction effect). This effect is used in thermocouples to measure temperature. The following are examples of thermojunctions on a PCB:

- Components (resistors, op amps) soldered to a copper pad
- · Wires mechanically attached to the PCB
- Jumpers
- · Solder joints
- PCB vias

Typical thermojunctions have temperature-to-voltage conversion coefficients of 1 to 100  $\mu\text{V}/^{\circ}\text{C}$  (sometimes higher).

Microchip's AN1258 "*Op Amp Precision Design: PCB Layout Techniques*" (DS01258) contains in-depth information on PCB layout techniques that minimize thermojunction effects. It also discusses other effects, such as crosstalk, impedances, mechanical stresses and humidity.

#### 4.3.10.2 Crosstalk

DC crosstalk causes offsets that appear as a larger input offset voltage. Common causes include:

- Common-mode noise (remote sensors)
- Ground loops (current return paths)
- Power supply coupling

Interference from the mains (usually 50 Hz or 60 Hz) and other AC sources can also affect the DC performance. Nonlinear distortion can convert these signals to multiple tones, including a DC shift in voltage. When the signal is sampled by an ADC, these AC signals can also be aliased to DC, causing an apparent shift in offset.

To reduce interference:

- · Keep traces and wires as short as possible
- · Use shielding
- Use ground plane (at least a star ground)
- · Place the input signal source near the DUT
- · Use good PCB layout techniques
- Use a separate power supply filter (bypass capacitors) for these zero-drift op amps

#### 4.3.10.3 Miscellaneous Effects

Keep the resistances seen by the input pins as small, and as near to equal, as possible to minimize bias current related offsets.

Make the (trace) capacitances seen by the input pins small and equal. This is helpful in minimizing switching glitch induced offset voltages.

Bending a coax cable with a radius that is too small causes a small voltage drop to appear on the center conductor (the triboelectric effect). Make sure the bending radius is large enough to keep the conductors and insulation in full contact.

Mechanical stresses can make some capacitor types (such as some ceramics) output small voltages. Use more appropriate capacitor types in the signal path and minimize mechanical stresses and vibration.

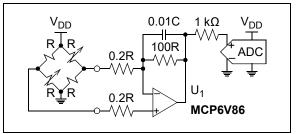
Humidity can cause electrochemical potential voltages to appear in a circuit. Proper PCB cleaning helps, as does the use of encapsulants.

#### 4.4 Typical Applications

#### 4.4.1 WHEATSTONE BRIDGE

Many sensors are configured as Wheatstone bridges. Strain gauges and pressure sensors are two common examples. These signals can be small and the Common-mode noise large. Amplifier designs with high differential gain are desirable.

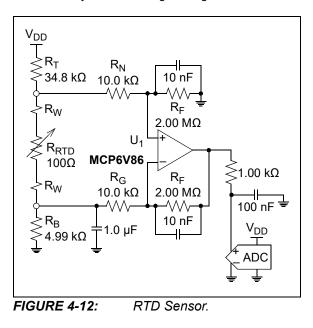
Figure 4-11 shows how to interface to a Wheatstone bridge with a minimum of components. Because the circuit is not symmetric, the ADC input is single-ended and there is a minimum of filtering; the CMRR is good enough for moderate Common-mode noise.





#### 4.4.2 RTD SENSOR

The ratiometric circuit in Figure 4-12 conditions a two-wire RTD for applications with a limited temperature range.  $U_1$  acts as a difference amplifier with a low-frequency pole. The sensor's Wiring Resistance ( $R_W$ ) is corrected in firmware. Failure (open) of the RTD is detected by an out-of-range voltage.



#### 4.4.3 OFFSET VOLTAGE CORRECTION

Figure 4-13 shows MCP6V86 (U<sub>2</sub>) correcting the input offset voltage of another op amp (U<sub>1</sub>). R<sub>2</sub> and C<sub>2</sub> integrate the offset error seen at U<sub>1</sub>'s input. The integration needs to be slow enough to be stable (with the feedback provided by R<sub>1</sub> and R<sub>3</sub>). R<sub>4</sub> and R<sub>5</sub> attenuate the integrator's output. This shifts the integrator pole down in frequency.

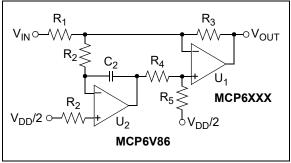
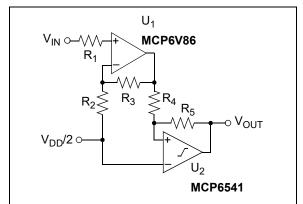


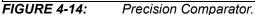
FIGURE 4-13:

Offset Correction.

#### 4.4.4 PRECISION COMPARATOR

Use high gain before a comparator to improve the latter's performance. Do not use the MCP6V86/6U/7/9 as a comparator by itself; the  $V_{OS}$  correction circuitry does not operate properly without a feedback loop.





NOTES:

#### 5.0 DESIGN AIDS

Microchip provides the basic design aids needed for the MCP6V86/6U/7/9 family of op amps.

### 5.1 Microchip Advanced Part Selector (MAPS)

MAPS is a software tool that helps efficiently identify Microchip devices that fit a particular design requirement. Available at no cost from the Microchip website at www.microchip.com/maps, MAPS is an overall selection tool for Microchip's product portfolio that includes Analog, Memory, MCUs and DSCs. Using this tool, a customer can define a filter to sort features for a parametric search of devices and export side-by-side technical comparison reports. Helpful links are also provided for data sheets, purchase and sampling of Microchip parts.

#### 5.2 Analog Demonstration and Evaluation Boards

Microchip offers a broad spectrum of Analog Demonstration and Evaluation Boards that are designed to help customers achieve faster time to market. For a complete listing of these boards, and their corresponding user's guides and technical information, visit the Microchip website at www.microchip.com/analog tools.

Some boards that are especially useful are:

- MCP6V01 Thermocouple Auto-Zeroed Reference Design (P/N MCP6V01RD-TCPL)
- MCP6XXX Amplifier Evaluation Board 2 (P/N DS51668)
- MCP6XXX Amplifier Evaluation Board 3 (P/N DS51673)
- 8-Pin SOIC/MSOP/TSSOP/DIP Evaluation Board (P/N SOIC8EV)
- 14-Pin SOIC/TSSOP/DIP Evaluation Board (P/N SOIC14EV)

#### 5.3 Application Notes

The following Microchip Application Notes are available on the Microchip website at www.microchip. com/appnotes and are recommended as supplemental reference resources.

**ADN003:** "Select the Right Operational Amplifier for your Filtering Circuits" (DS21821)

**AN722:** "Operational Amplifier Topologies and DC Specifications" (DS00722)

**AN723:** "Operational Amplifier AC Specifications and Applications" (DS00723)

**AN884:** "Driving Capacitive Loads With Op Amps" (DS00884)

**AN990:** "Analog Sensor Conditioning Circuits – An Overview" (DS00990)

**AN1177:** "Op Amp Precision Design: DC Errors" (DS01177)

AN1228: "Op Amp Precision Design: Random Noise" (DS01228)

**AN1258:** "Op Amp Precision Design: PCB Layout Techniques" (DS01258)

**AN1767:** "Solutions for Radio Frequency Electromagnetic Interference in Amplifier Circuits" (DS01767A)

These Application Notes and others are listed in the design guide:

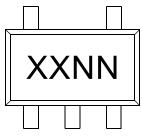
"Signal Chain Design Guide" (DS21825)

NOTES:

#### 6.0 **PACKAGING INFORMATION**

#### 6.1 **Package Marking Information**

5-Lead SC70 (MCP6V86U)



5-Lead SOT-23 (MCP6V86, MCP6V86U)

Device	Code
MCP6V86UT-E/LTY	FZNN

Device

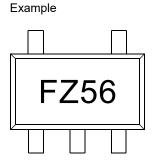
MCP6V86T-E/OT

MCP6V86UT-E/OT

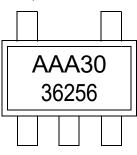
Code

AAA3Y

AAA4Y



## Example AAA30 36256



8-Lead MSOP (MCP6V87)

XXXXY

**WWNNN** 

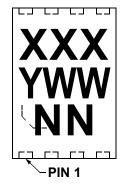




Legend:	XXX	Customer-specific information
	Υ	Year code (last digit of calendar year)
	YY	Year code (last 2 digits of calendar year)
	WW	Week code (week of January 1 is week '01')
	NNN	Alphanumeric traceability code
	(e3)	Pb-free JEDEC <sup>®</sup> designator for Matte Tin (Sn)
	*	This package is Pb-free. The Pb-free JEDEC designator (e3) can be found on the outer packaging for this package.
b	e carrie	nt the full Microchip part number cannot be marked on one line, it will d over to the next line, thus limiting the number of available for customer-specific information.

© 2020 Microchip Technology Inc.

#### 8-Lead TDFN (MCP6V87)

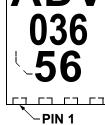


Device	Code
MCP6V87T-E/MNY	ADV

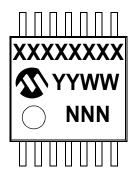
Note: Applies to 8-Lead 2x3 TDFN.

# ADV

Example



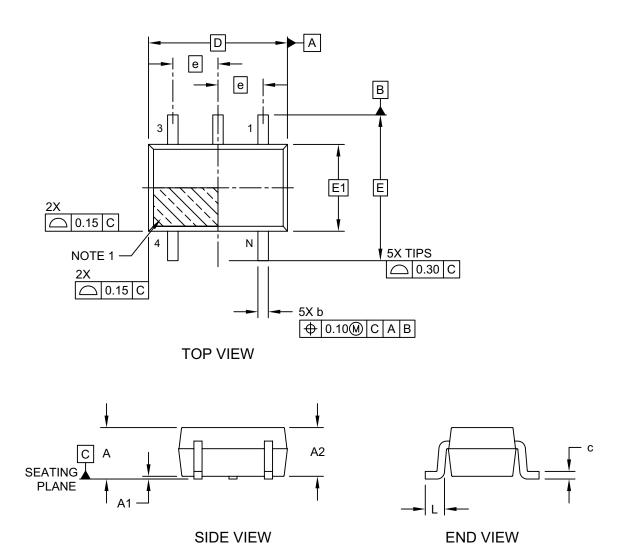
14-Lead TSSOP (MCP6V89)





#### 5-Lead Plastic Small Outline Transistor (LTY) [SC70]

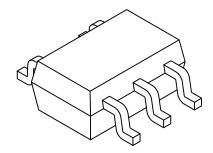
**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing C04-061-LTY Rev E Sheet 1 of 2

#### 5-Lead Plastic Small Outline Transistor (LTY) [SC70]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	N	<b>IILLIMETER</b>	S		
Dimension	MIN	NOM	MAX		
Number of Pins	N		5		
Pitch	е		0.65 BSC		
Overall Height	Α	0.80 - 1.10			
Standoff	A1	0.00	-	0.10	
Molded Package Thickness	A2	0.80	-	1.00	
Overall Length	D	2.00 BSC			
Overall Width	E		2.10 BSC		
Molded Package Width	E1	1.25 BSC			
Terminal Width	b	0.15	-	0.40	
Terminal Length	L	0.10	0.20	0.46	
Lead Thickness	С	0.08	-	0.26	

#### Notes:

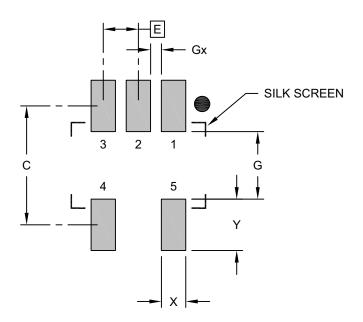
- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or
- protrusions shall not exceed 0.15mm per side. 3. Dimensioning and tolerancing per ASME Y14.5M
  - BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-061-LTY Rev E Sheet 2 of 2

#### 5-Lead Plastic Small Outline Transistor (LTY) [SC70]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



#### RECOMMENDED LAND PATTERN

	Units	Ν	ILLIMETER	S
Dimension	Limits	MIN	NOM	MAX
Contact Pitch	E		0.65 BSC	
Contact Pad Spacing	С		2.20	
Contact Pad Width				0.45
Contact Pad Length				0.95
Distance Between Pads	G	1.25		
Distance Between Pads	Gx	0.20		

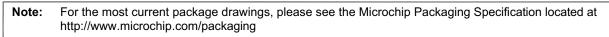
#### Notes:

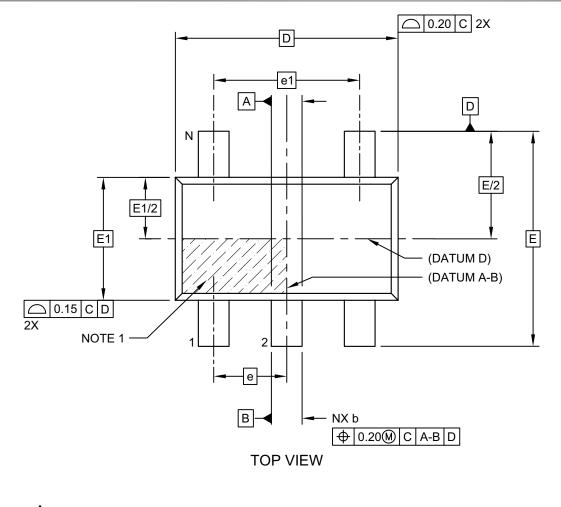
1. Dimensioning and tolerancing per ASME Y14.5M

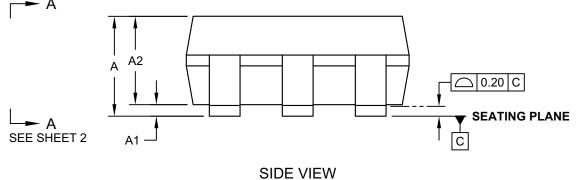
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2061-LTY Rev E

### 5-Lead Plastic Small Outline Transistor (OT) [SOT23]



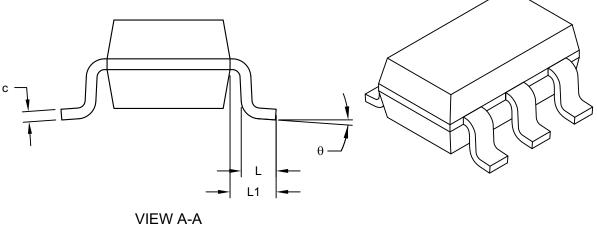




Microchip Technology Drawing C04-091-OT Rev F Sheet 1 of 2

#### 5-Lead Plastic Small Outline Transistor (OT) [SOT23]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



SHEET 1

	Units	MILLIMETERS			
Dimension Limits		MIN	NOM	MAX	
Number of Pins	N	5			
Pitch	е	0.95 BSC			
Outside lead pitch	e1	1.90 BSC			
Overall Height	A	0.90	-	1.45	
Molded Package Thickness	A2	0.89	-	1.30	
Standoff	A1	-	-	0.15	
Overall Width	E	2.80 BSC			
Molded Package Width	E1	1.60 BSC			
Overall Length	D	2.90 BSC			
Foot Length	L	0.30	-	0.60	
Footprint	L1	0.60 REF			
Foot Angle	¢	0°	-	10°	
Lead Thickness	С	0.08	-	0.26	
Lead Width	b	0.20	-	0.51	

Notes:

1. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.25mm per side.

2. Dimensioning and tolerancing per ASME Y14.5M

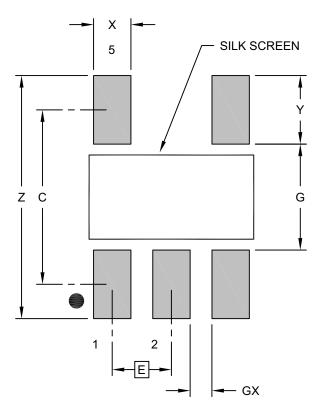
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-091-OT Rev F Sheet 2 of 2

#### 5-Lead Plastic Small Outline Transistor (OT) [SOT23]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



#### RECOMMENDED LAND PATTERN

	Units		MILLIMETERS			
Dimension Limits		MIN	NOM	MAX		
Contact Pitch	E	0.95 BSC				
Contact Pad Spacing	С		2.80			
Contact Pad Width (X5)	Х			0.60		
Contact Pad Length (X5)	Y			1.10		
Distance Between Pads	G	1.70				
Distance Between Pads	GX	0.35				
Overall Width	Z			3.90		

Notes:

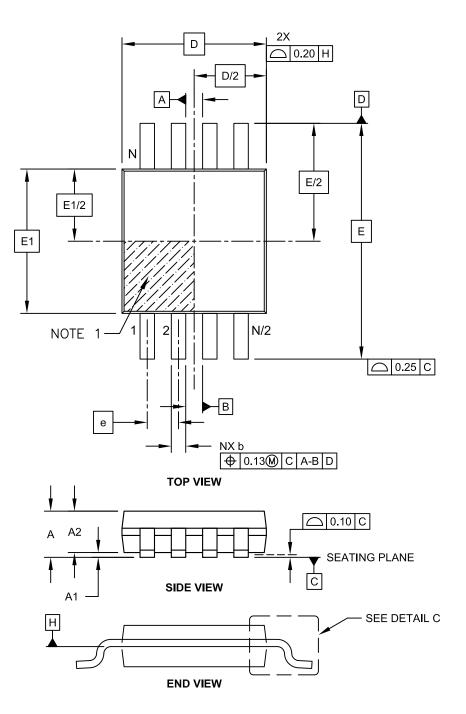
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2091-OT Rev F

### 8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

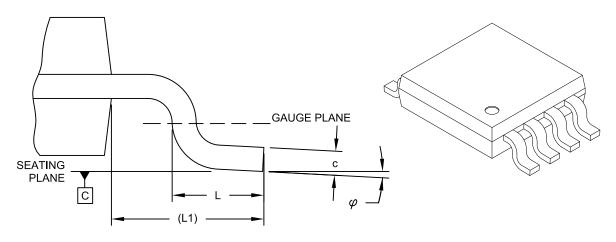
**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing C04-111C Sheet 1 of 2

### 8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



DETAIL C

	MILLIMETERS				
Dimensior	Dimension Limits		NOM	MAX	
Number of Pins	Ν		8		
Pitch	е		0.65 BSC		
Overall Height	Α	-	-	1.10	
Molded Package Thickness	A2	0.75	0.85	0.95	
Standoff	A1	0.00	-	0.15	
Overall Width	Е	4.90 BSC			
Molded Package Width	E1	3.00 BSC			
Overall Length	D	3.00 BSC			
Foot Length	L	0.40	0.60	0.80	
Footprint	L1	0.95 REF			
Foot Angle	φ	0°	-	8°	
Lead Thickness	С	0.08	-	0.23	
Lead Width	b	0.22	-	0.40	

#### Notes:

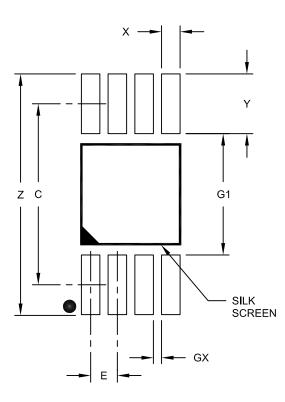
1. Pin 1 visual index feature may vary, but must be located within the hatched area.

- 2. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or
- protrusions shall not exceed 0.15mm per side.
- Dimensioning and tolerancing per ASME Y14.5M.
   BSC: Basic Dimension. Theoretically exact value shown without tolerances.
   REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-111C Sheet 2 of 2

### 8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



### RECOMMENDED LAND PATTERN

	Units		MILLIMETERS		
Dimensior	Dimension Limits		NOM	MAX	
Contact Pitch	E	0.65 BSC			
Contact Pad Spacing	С		4.40		
Overall Width	Z			5.85	
Contact Pad Width (X8)	X1			0.45	
Contact Pad Length (X8)	Y1			1.45	
Distance Between Pads	G1	2.95			
Distance Between Pads	GX	0.20			

Notes:

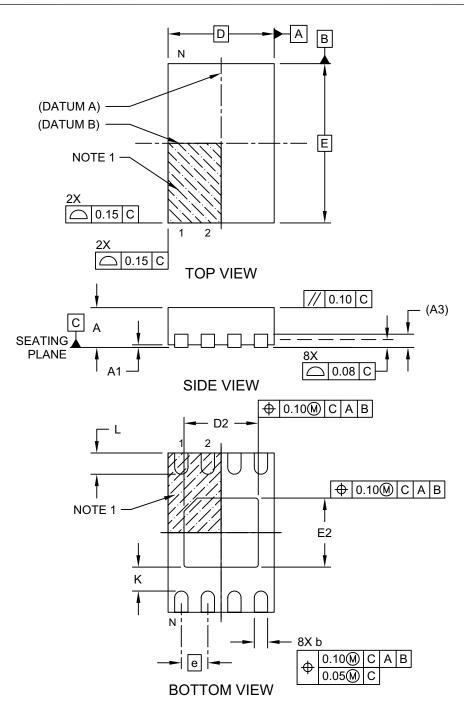
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2111A

### 8-Lead Plastic Dual Flat, No Lead Package (MNY) – 2x3x0.8 mm Body [TDFN] With 1.4x1.3 mm Exposed Pad (JEDEC Package type WDFN)

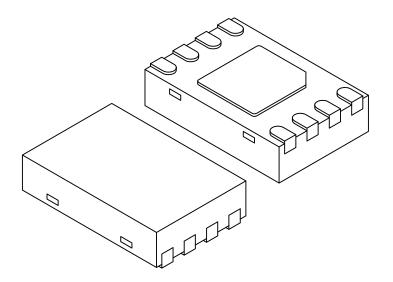
**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing No. C04-129-MNY Rev E Sheet 1 of 2

### 8-Lead Plastic Dual Flat, No Lead Package (MNY) – 2x3x0.8 mm Body [TDFN] With 1.4x1.3 mm Exposed Pad (JEDEC Package type WDFN)

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Units		MILLIMETERS			
Dimension Limits		MIN	NOM	MAX	
Number of Pins	N	8			
Pitch	е		0.50 BSC		
Overall Height	Α	0.70 0.75 0.80			
Standoff	A1	0.00 0.02 0.05			
Contact Thickness	A3	0.20 REF			
Overall Length	D	2.00 BSC			
Overall Width	E	3.00 BSC			
Exposed Pad Length	D2	1.35	1.40	1.45	
Exposed Pad Width	E2	1.25	1.30	1.35	
Contact Width	b	0.20 0.25 0.30			
Contact Length	L	0.25 0.30 0.45			
Contact-to-Exposed Pad	К	0.20			

### Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. Package may have one or more exposed tie bars at ends.

3. Package is saw singulated

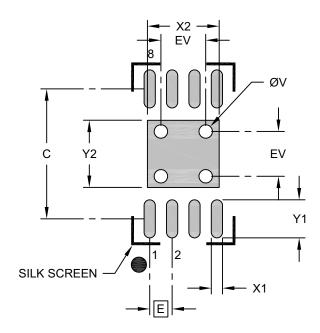
4. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances. REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-129-MNY Rev E Sheet 2 of 2

### 8-Lead Plastic Dual Flat, No Lead Package (MNY) – 2x3x0.8 mm Body [TDFN] With 1.4x1.3 mm Exposed Pad (JEDEC Package type WDFN)

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



### RECOMMENDED LAND PATTERN

Units		MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Contact Pitch	Е	0.50 BSC		
Optional Center Pad Width	X2			1.60
Optional Center Pad Length	Y2			1.50
Contact Pad Spacing	С		2.90	
Contact Pad Width (X8)	X1			0.25
Contact Pad Length (X8)	Y1			0.85
Thermal Via Diameter	V		0.30	
Thermal Via Pitch	EV		1.00	

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

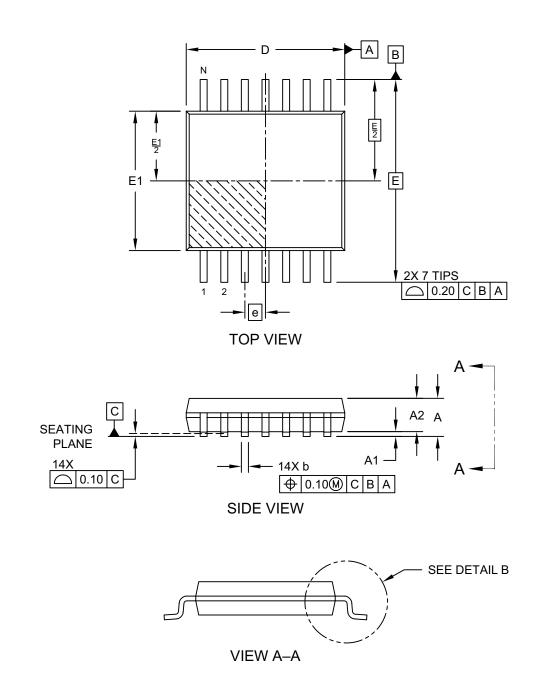
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

2. For best soldering results, thermal vias, if used, should be filled or tented to avoid solder loss during reflow process

Microchip Technology Drawing No. C04-129-MNY Rev. B

### 14-Lead Thin Shrink Small Outline Package [ST] 4.4 mm Body [TSSOP]

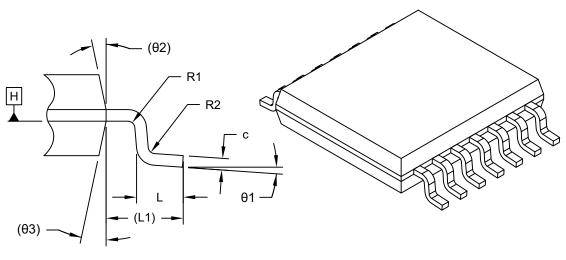
**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing C04-087 Rev D Sheet 1 of 2

### 14-Lead Thin Shrink Small Outline Package [ST] 4.4 mm Body [TSSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



DE.	TAI	LΒ

	MILLIMETERS			
Dimensio	n Limits	MIN	NOM	MAX
Number of Terminals	N	14		
Pitch	е	0.65 BSC		
Overall Height	А	-	-	1.20
Standoff	A1	0.05	_	0.15
Molded Package Thickness	A2	0.80	1.00	1.05
Overall Length	D	4.90	5.00	5.10
Overall Width	E	6.40 BSC		
Molded Package Width	E1	4.30	4.40	4.50
Terminal Width	b	0.19	_	0.30
Terminal Thickness	С	0.09	-	0.20
Terminal Length	L	0.45	0.60	0.75
Footprint	L1	1.00 REF		
Lead Bend Radius	R1	0.09	-	_
Lead Bend Radius	R2	0.09	-	_
Foot Angle	θ1	0°	_	8°
Mold Draft Angle	θ2	_	12° REF	_
Mold Draft Angle	θ3	-	12° REF	-

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. Dimensioning and tolerancing per ASME Y14.5M

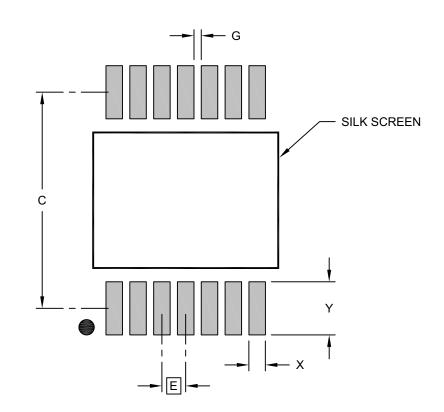
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-087 Rev D Sheet 2 of 2

### 14-Lead Thin Shrink Small Outline Package [ST] 4.4 mm Body [TSSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



### RECOMMENDED LAND PATTERN

	Units		MILLIMETERS		
Dimension	Dimension Limits		NOM	MAX	
Contact Pitch	E	0.65 BSC			
Contact Pad Spacing	С		5.90		
Contact Pad Width (Xnn)	Х			0.45	
Contact Pad Length (Xnn)	Y			1.45	
Contact Pad to Contact Pad (Xnn)	G	0.20			

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-2087 Rev D

# MCP6V86/6U/7/9

NOTES:

## APPENDIX A: REVISION HISTORY

## Revision A (August 2020)

• Original Release of this Document.

# MCP6V86/6U/7/9

NOTES:

## **PRODUCT IDENTIFICATION SYSTEM**

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

PART NO. [X]	<sup>(1)</sup> –X /XX	Exar	nples:	
Device Tape and		a)	MCP6V86T-E/OT:	Tape and Reel, Extended Temperature, 5-Lead SOT-23 Package
Device:	MCP6V86: Single Op Amp (SOT-23 only)	a)	MCP6V86UT-E/LTY:	Tape and Reel Extended Temperature, 5-Lead SC70 Package
	MCP6V86U:Single Op Amp (SC70, SOT-23)MCP6V87:Dual Op Amp (MSOP, TDFN)MCP6V89:Quad Op Amp (TSSOP)	b)	MCP6V86UT-E/OT:	Tape and Reel, Extended Temperature, 5-Lead SOT-23 Package
Tape and Reel	T = Tape and Reel	a)	MCP6V87-E/MS:	Extended Temperature, 8-Lead MSOP Package
Temperature Range:	E = $-40^{\circ}$ C to $+125^{\circ}$ C (Extended)	b)	MCP6V87T-E/MS:	Tape and Reel, Extended Temperature, 8-Lead MSOP Package
Package:	LTY* = Plastic Small Outline Transistor, SC70, 5-Lead OT = Plastic Small Outline Transistor, SOT-23, 5-Lead	c)	MCP6V87T-E/MNY:	Tape and Reel, Extended Temperature, 8-Lead 2 x 3 TDFN Package
	MNY* = Plastic Dual Flat, No Lead – 2x3x0.8 mm TDFN, 8-Lead	a)	MCP6V89-E/ST:	Extended Temperature, 14-Lead TSSOP Package
	MS = Plastic Micro Small Outline, MSOP, 8-Lead ST = Thin Shrink Small Outline – 4.4 mm TSSOP, 14-Lead	b)	MCP6V89T-E/ST:	Tape and Reel, Extended Temperature, 14-Lead TSSOP Package
	*Y = Nickel palladium gold manufacturing designator. Only available on the SC70 and TDFN packages.	Note	catalog part nu fier is used for printed on the o your Microchip	identifier only appears in the mber description. This identi- ordering purposes and is not jevice package. Check with Sales Office for package the Tape and Reel option.

# MCP6V86/6U/7/9

NOTES:

#### Note the following details of the code protection feature on Microchip devices:

- · Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as "unbreakable."

Code protection is constantly evolving. We at Microchip are committed to continuously improving the code protection features of our products. Attempts to break Microchip's code protection feature may be a violation of the Digital Millennium Copyright Act. If such acts allow unauthorized access to your software or other copyrighted work, you may have a right to sue for relief under that Act.

Information contained in this publication regarding device applications and the like is provided only for your convenience and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications. MICROCHIP MAKES NO REPRESENTATIONS OR WARRANTIES OF ANY KIND WHETHER EXPRESS OR IMPLIED, WRITTEN OR ORAL, STATUTORY OR OTHERWISE, RELATED TO THE INFORMATION, INCLUDING BUT NOT LIMITED TO ITS CONDITION, QUALITY, PERFORMANCE, MERCHANTABILITY OR FITNESS FOR PURPOSE. Microchip disclaims all liability arising from this information and its use. Use of Microchip devices in life support and/or safety applications is entirely at the buyer's risk, and the buyer agrees to defend, indemnify and hold harmless Microchip from any and all damages, claims, suits, or expenses resulting from such use. No licenses are conveyed, implicitly or otherwise, under any Microchip intellectual property rights unless otherwise stated.

#### Trademarks

The Microchip name and logo, the Microchip logo, Adaptec, AnyRate, AVR, AVR logo, AVR Freaks, BesTime, BitCloud, chipKIT, chipKIT logo, CryptoMemory, CryptoRF, dsPIC, FlashFlex, flexPWR, HELDO, IGLOO, JukeBlox, KeeLoq, Kleer, LANCheck, LinkMD, maXStylus, maXTouch, MediaLB, megaAVR, Microsemi, Microsemi logo, MOST, MOST logo, MPLAB, OptoLyzer, PackeTime, PIC, picoPower, PICSTART, PIC32 logo, PolarFire, Prochip Designer, QTouch, SAM-BA, SenGenuity, SpyNIC, SST, SST Logo, SuperFlash, Symmetricom, SyncServer, Tachyon, TempTrackr, TimeSource, tinyAVR, UNI/O, Vectron, and XMEGA are registered trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

APT, ClockWorks, The Embedded Control Solutions Company, EtherSynch, FlashTec, Hyper Speed Control, HyperLight Load, IntelliMOS, Libero, motorBench, mTouch, Powermite 3, Precision Edge, ProASIC, ProASIC Plus, ProASIC Plus logo, Quiet-Wire, SmartFusion, SyncWorld, Temux, TimeCesium, TimeHub, TimePictra, TimeProvider, Vite, WinPath, and ZL are registered trademarks of Microchip Technology Incorporated in the U.S.A.

Adjacent Key Suppression, AKS, Analog-for-the-Digital Age, Any Capacitor, AnyIn, AnyOut, BlueSky, BodyCom, CodeGuard, CryptoAuthentication, CryptoAutomotive, CryptoCompanion, CryptoController, dsPICDEM, dsPICDEM.net, Dynamic Average Matching, DAM, ECAN, EtherGREEN, In-Circuit Serial Programming, ICSP, INICnet, Inter-Chip Connectivity, JitterBlocker, KleerNet, KleerNet Iogo, memBrain, Mindi, MiWi, MPASM, MPF, MPLAB Certified Iogo, MPLIB, MPLINK, MultiTRAK, NetDetach, Omniscient Code Generation, PICDEM, PICDEM.net, PICkit, PICtail, PowerSmart, PureSilicon, QMatrix, REAL ICE, Ripple Blocker, SAM-ICE, Serial Quad I/O, SMART-I.S., SQI, SuperSwitcher, SuperSwitcher II, Total Endurance, TSHARC, USBCheck, VariSense, ViewSpan, WiperLock, Wireless DNA, and ZENA are trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

SQTP is a service mark of Microchip Technology Incorporated in the U.S.A.

The Adaptec logo, Frequency on Demand, Silicon Storage Technology, and Symmcom are registered trademarks of Microchip Technology Inc. in other countries.

GestIC is a registered trademark of Microchip Technology Germany II GmbH & Co. KG, a subsidiary of Microchip Technology Inc., in other countries.

All other trademarks mentioned herein are property of their respective companies.

© 2020, Microchip Technology Incorporated, All Rights Reserved.

ISBN: 978-1-5224-6594-2

For information regarding Microchip's Quality Management Systems, please visit www.microchip.com/quality.



## Worldwide Sales and Service

### AMERICAS

**Corporate Office** 2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-792-7200 Fax: 480-792-7277 **Technical Support:** http://www.microchip.com/ support

Web Address: www.microchip.com

Atlanta Duluth, GA Tel: 678-957-9614 Fax: 678-957-1455

Austin, TX Tel: 512-257-3370

**Boston** Westborough, MA Tel: 774-760-0087 Fax: 774-760-0088

Chicago Itasca, IL Tel: 630-285-0071 Fax: 630-285-0075

Dallas Addison, TX Tel: 972-818-7423 Fax: 972-818-2924

Detroit Novi, MI Tel: 248-848-4000

Houston, TX Tel: 281-894-5983

Indianapolis Noblesville, IN Tel: 317-773-8323 Fax: 317-773-5453 Tel: 317-536-2380

Los Angeles Mission Viejo, CA Tel: 949-462-9523 Fax: 949-462-9608 Tel: 951-273-7800

Raleigh, NC Tel: 919-844-7510

New York, NY Tel: 631-435-6000

San Jose, CA Tel: 408-735-9110 Tel: 408-436-4270

Canada - Toronto Tel: 905-695-1980 Fax: 905-695-2078

### ASIA/PACIFIC

Australia - Sydney Tel: 61-2-9868-6733

China - Beijing Tel: 86-10-8569-7000 China - Chengdu

Tel: 86-28-8665-5511 China - Chongqing Tel: 86-23-8980-9588

China - Dongguan Tel: 86-769-8702-9880

China - Guangzhou Tel: 86-20-8755-8029

China - Hangzhou Tel: 86-571-8792-8115

China - Hong Kong SAR Tel: 852-2943-5100

China - Nanjing Tel: 86-25-8473-2460

China - Qingdao Tel: 86-532-8502-7355

China - Shanghai Tel: 86-21-3326-8000

China - Shenyang Tel: 86-24-2334-2829

China - Shenzhen Tel: 86-755-8864-2200

China - Suzhou Tel: 86-186-6233-1526

China - Wuhan Tel: 86-27-5980-5300

China - Xian Tel: 86-29-8833-7252

China - Xiamen Tel: 86-592-2388138 China - Zhuhai

Tel: 86-756-3210040

### ASIA/PACIFIC

India - Bangalore Tel: 91-80-3090-4444

India - New Delhi Tel: 91-11-4160-8631 India - Pune

Tel: 91-20-4121-0141 Japan - Osaka

Tel: 81-6-6152-7160 Japan - Tokyo

Tel: 81-3-6880- 3770 Korea - Daegu

Tel: 82-53-744-4301 Korea - Seoul

Tel: 82-2-554-7200

Malaysia - Kuala Lumpur Tel: 60-3-7651-7906

Malaysia - Penang Tel: 60-4-227-8870

Tel: 63-2-634-9065

Singapore Tel: 65-6334-8870

Taiwan - Hsin Chu Tel: 886-3-577-8366

Taiwan - Kaohsiung Tel: 886-7-213-7830

Tel: 84-28-5448-2100

Italy - Padova Tel: 39-049-7625286

EUROPE

Austria - Wels

Tel: 43-7242-2244-39

Tel: 45-4485-5910

Fax: 45-4485-2829

Tel: 358-9-4520-820

Tel: 33-1-69-53-63-20

Fax: 33-1-69-30-90-79

Germany - Garching

Tel: 49-2129-3766400

Germany - Heilbronn

Germany - Karlsruhe

Tel: 49-7131-72400

Tel: 49-721-625370

Germany - Munich

Tel: 49-89-627-144-0

Fax: 49-89-627-144-44

Germany - Rosenheim

Tel: 49-8031-354-560

Israel - Ra'anana

Italy - Milan

Tel: 972-9-744-7705

Tel: 39-0331-742611

Fax: 39-0331-466781

Tel: 49-8931-9700

Germany - Haan

Finland - Espoo

France - Paris

Fax: 43-7242-2244-393

Denmark - Copenhagen

**Netherlands - Drunen** Tel: 31-416-690399 Fax: 31-416-690340

Norway - Trondheim Tel: 47-7288-4388

Poland - Warsaw Tel: 48-22-3325737

Romania - Bucharest Tel: 40-21-407-87-50

Spain - Madrid Tel: 34-91-708-08-90 Fax: 34-91-708-08-91

Sweden - Gothenberg Tel: 46-31-704-60-40

Sweden - Stockholm Tel: 46-8-5090-4654

**UK - Wokingham** Tel: 44-118-921-5800 Fax: 44-118-921-5820

Philippines - Manila

Vietnam - Ho Chi Minh

Tel: 66-2-694-1351

Taiwan - Taipei Tel: 886-2-2508-8600

Thailand - Bangkok